

About this file: EP0482648

EP0482648 - Method of vapour growing a semiconductor crystal [Right-click to bookmark this link]			
Status	No opposition filed within time limit <i>Status updated on 06.12.2002</i> <i>Database last updated on 28.04.2021</i>		
Most recent event	06.12.2002	No opposition filed within time limit	published on 22.01.2003 [2003/04]
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Representative(s)	von Bezold, Dieter , et al v. Bezold & Partner Patentanwälte Akademiestrasse 7 80799 München / DE [N/P]		
Application number, filing date	91118176.6 [1992/18]	24.10.1991	
Priority number, date	JP19900288665 JP19910074822 [1992/18]	25.10.1990 Original published format: JP 28866590 13.03.1991 Original published format: JP 7482291	
Filing language	EN		
Procedural language	EN		
Publication	Type:	A1 Application with search report	
	No.:	EP0482648	
	Date:	29.04.1992	
	Language:	EN	
	[1992/18]		
	Type:	B1 Patent specification	
	No.:	EP0482648	
	Date:	30.01.2002	
Language:	EN		
[2002/05]			
Search report(s)	(Supplementary) European search report - dispatched on:	EP	29.01.1992
Classification	International:	H01L21/205, C30B25/14, C23C16/44	[1992/18]
Designated contracting states	DE, FR, GB, IT, NL [1992/18]		
Title	German:	Verfahren zur Dampfabseidung eines Halbleiterkristalls	[1999/37]
	English:	Method of vapour growing a semiconductor crystal	[2001/27]
	French:	Méthode de croissance d'un cristal semiconducteur	[1999/37]
Examination procedure	24.10.1991		Examination requested [1992/18]
	11.02.1994		Despatch of a communication from the examining division (Time limit: M06)
	17.08.1994		Reply to a communication from the examining division
	06.09.1995		Despatch of a communication from the examining division (Time limit: M06)
	04.03.1996		Reply to a communication from the examining division

	20.08.1997	Despatch of a communication from the examining division (Time limit: M06)
	27.02.1998	Reply to a communication from the examining division
	11.03.1999	Despatch of a communication from the examining division (Time limit: M04)
	01.07.1999	Reply to a communication from the examining division
	13.06.2001	Despatch of communication of intention to grant (Approval: Yes)
	18.07.2001	Communication of intention to grant the patent
	10.10.2001	Fee for grant paid
	10.10.2001	Fee for publishing/printing paid
Opposition(s)	31.10.2002	No opposition filed within time limit [2003/04]
Fees paid	Renewal fee	
	13.10.1993	Renewal fee patent year 03
	19.10.1994	Renewal fee patent year 04
	27.10.1995	Renewal fee patent year 05
	25.10.1996	Renewal fee patent year 06
	24.10.1997	Renewal fee patent year 07
	29.10.1998	Renewal fee patent year 08
	27.10.1999	Renewal fee patent year 09
	27.10.2000	Renewal fee patent year 10
17.10.2001	Renewal fee patent year 11	
Documents cited:	Search	[A]JP57186322 ;
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	Examination	